

DERWENT-ACC-NO: 2001-511244

DERWENT-WEEK: 200156

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TITLE: Sputtering target for semiconductor

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PATENT-ASSIGNEE: HYUNDAI MICROELECTRONICS CO LTD[HYUNN]

PRIORITY-DATA: 1999KR-0032332 (August 6, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES MAIN-IPC		
KR 2001017037 A	March 5, 2001	N/A
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APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
KR2001017037A	N/A	1999KR-0032332
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INT-CL (IPC): H01L021/20

ABSTRACTED-PUB-NO: KR2001017037A

BASIC-ABSTRACT:

NOVELTY - A sputtering target for a semiconductor is provided to remarkably reduce a foreign substance and to improve yield of a wafer, by rounding a corner of a portion necessary for sputtering.

DETAILED DESCRIPTION - A corner portion(10a) of a portion necessary for sputtering is processed to be round. A radius of curvature of the rounded portion is twice a radius of a sputtering target(10) used in evaporating an aluminum layer. When the corner of the target is round, a plasma region is reduced and plasma density becomes high. Plasma is lightly formed in the

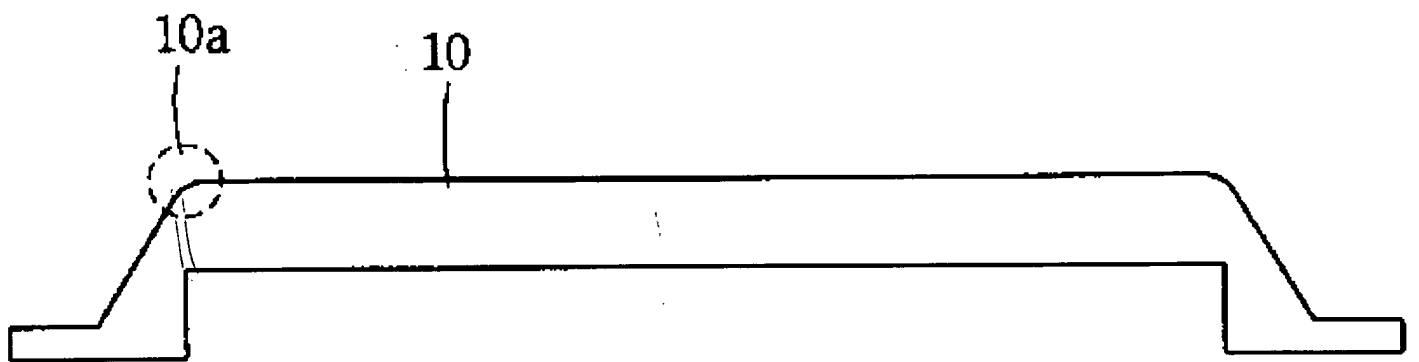
corner portion or in a front surface of the target so that a
blackening
phenomenon is reduced.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: SPUTTER TARGET SEMICONDUCTOR

DERWENT-CLASS: U11

EPI-CODES: U11-C01J1;



3/12

7-6"

1/2 in
2.5 cm
1 in